μ**PA2660T1**R

DUAL N-CHANNEL MOSFET

20 V, 4.0 A, 42 m Ω

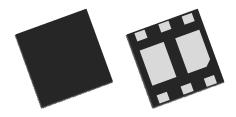
Description

The μ PA2660T1R is Dual N-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- DS MAXIMUM RATINGS $20V(T_A = 25^{\circ}C)$
- 2.5V drive available
- Low on-state resistance
 - ---- $R_{DS \mbox{ (on)}1}$ = 42 m Ω MAX. (V_{GS} = 4.5 V, I_D = 2.0 A)
 - ---- $R_{DS (on)2} = 62 \text{ m}\Omega \text{ MAX.} (V_{GS} = 2.5 \text{ V}, I_D = 2.0 \text{ A})$
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020(Dual)

Ordering Information

Part Number	Package		
μPA2660T1R-E2-AX* ¹	6pinHUSON2020(Dual)		

Note: *1.Pb-free (This product does not contain Pb in the external electrode and other parts.)

Absolute Maximum Ratings (T_A = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V_{GS} = 0 V)	V _{DSS}	20	V
Gate to Source Voltage ($V_{DS} = 0 V$)	V _{GSS}	±12	V
Drain Current (DC)	I _{D(DC)}	±4.0	А
Drain Current (pulse) *1	I _{D(pulse)}	±16	А
Total Power Dissipation (1 unit, 5 s) *2	P _{T1}	1.5	W
Total Power Dissipation (2 units, 5 s) *2	P _{T2}	2.3	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Notes: *1. PW≤10 μ s, Duty Cycle≤1%

*2. Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt

Caution: This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

 V_{ESD} = ±400V MIN. (C = 100pF, R = 1.5K Ω)

R07DS0999EJ0100

Rev.1.00

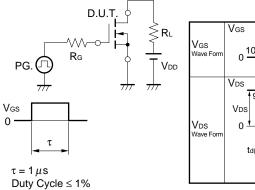
Jan 16, 2013

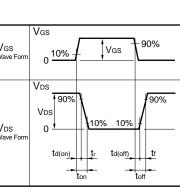
Electrical Characteristics (T_A = 25°C)

Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions	
Zero Gate Voltage Drain Current	I _{DSS}			1.0	μA	V _{DS} = 20 V, V _{GS} = 0 V	
Gate Leakage Current	I _{GSS}			±10	μA	V_{GS} = ±10 V, V_{DS} = 0 V	
Gate Cut-off Voltage	V _{GS(off)}	0.5		1.5	V	V _{DS} = 10 V, I _D = 1 mA	
Forward Transfer Admittance *1	y _{fs}	5.0			S	V_{DS} = 10 V, I_{D} = 2.0 A	
Drain to Source On-state	R _{DS(on)1}		33	42	mΩ	V_{GS} = 4.5 V, I _D = 2.0 A	
Resistance *1	R _{DS(on)2}		43	62	mΩ	V_{GS} = 2.5 V, I _D = 2.0 A	
Input Capacitance	C _{iss}		330		pF	V _{DS} = 10 V, V _{GS} = 0 V, f = 1.0 MHz	
Output Capacitance	C _{oss}		66		pF		
Reverse Transfer Capacitance	C _{rss}		38		pF		
Turn-on Delay Time	t _{d (on)}		12		ns	I _D = 2.0 A, V _{DD} = 10 V,	
Rise Time	t _r		6.4		ns	V_{GS} = 4.5 V, R_{G} = 6 Ω	
Turn-off Delay Time	t _{d (off)}		27		ns		
Fall Time	t _f		6.6		ns		
Total Gate Charge	Q _G		4.5		nC	I _D = 4.0 A , V _{DD} = 16 V, V _{GS} = 10 V	
Gate to Source Charge	Q _{GS}		1.0		nC		
Gate to Drain Charge	Q _{GD}		1.5		nC		
Body Diode Forward Voltage *1	V _{F(S-D)}			1.5	V	I _F = 4.0 A, V _{GS} = 0 V	

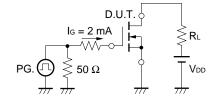
Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME





TEST CIRCUIT 2 GATE CHARGE

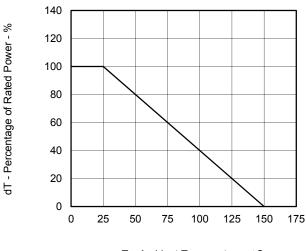




I_D – Drain Current - A

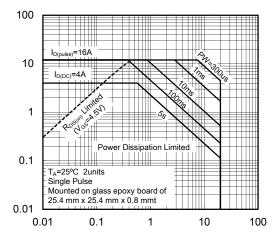
Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

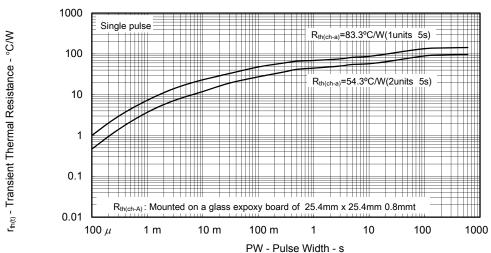


T_A -Ambient Temperature - °C





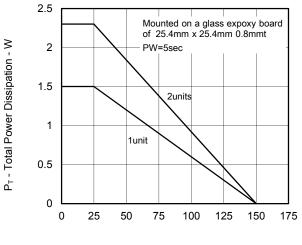




TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

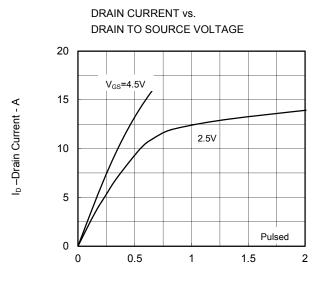
AMBIENT TEMPERATURE

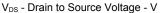
TOTAL POWER DISSIPATION vs.

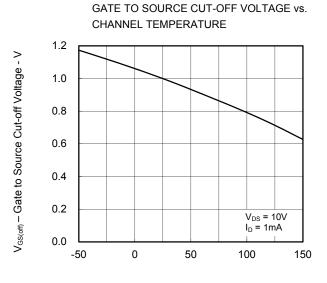


T_A -Ambient Temperature - °C

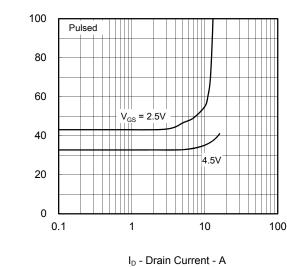






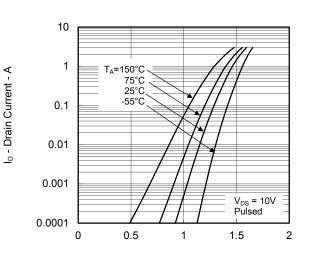


T_{ch} - Channel Temperature - °C

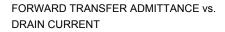


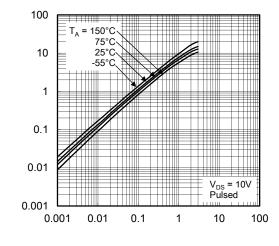
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

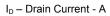
FORWARD TRANSFER CHARACTERISTICS

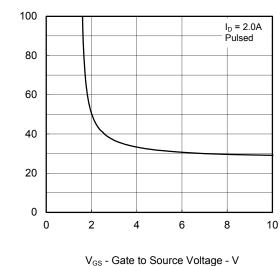


V_{GS} - Gate to Source Voltage - V









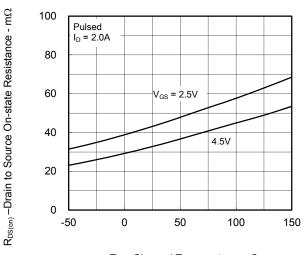
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

$R_{\text{DS}(\text{on})}$ - Drain to Source On-state Resistance - $m\Omega$



| y_{fs} | - Forward Transfer Admittance - S

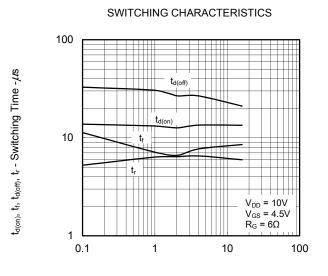
 $R_{\text{DS(on)}}$ – Drain to Source On-state Resistance - $m\Omega$

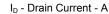


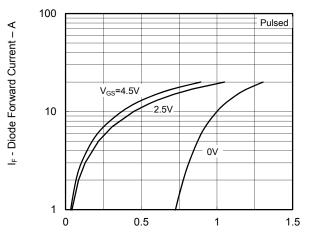
DRAIN TO SOURCE ON-STATE RESISTANCE vs.

CHANNEL TEMPERATURE

T_{ch} - Channel Temperature - °C



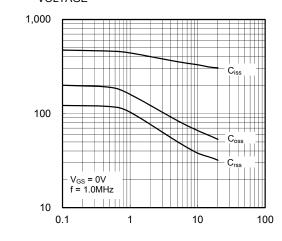




SOURCE TO DRAIN DIODE FORWARD VOLTAGE

 $V_{F(S\!-\!D)}$ - Drain to Source Voltage - V

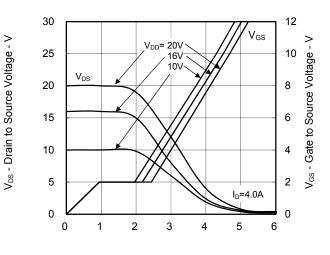
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



Ciss, Coss, Crss - Capacitance - pF

V_{DS} – Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

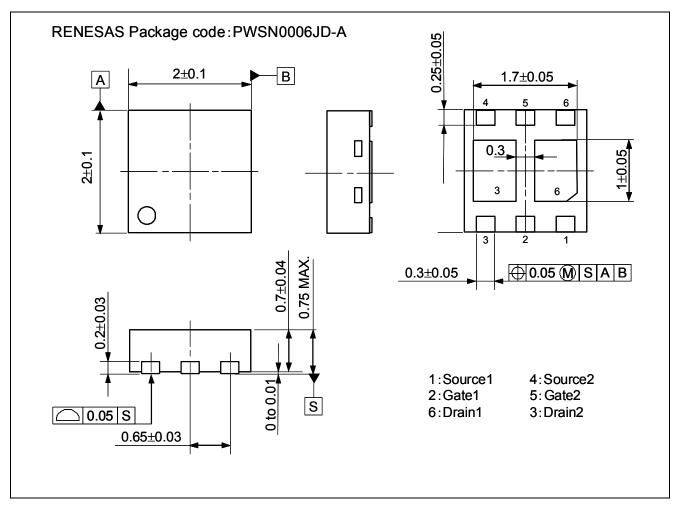


Q_G - Gate Charge - nC

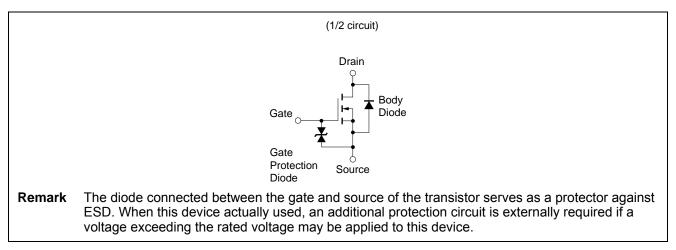


Package Drawings (Unit: mm)

6pinHUSON2020



Equivalent Circuit





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